TRENCH TRANSISTOR

ABSTRACT

A method of forming a device is disclosed. A substrate defined with a device region is provided. A buried doped region is formed in the substrate in the device region. A gate is formed in a trench in the substrate in the device region. A channel of the device is disposed on a sidewall of the trench. The buried doped region is disposed below the gate. A distance from the buried doped region to the channel is a drift length L_D of the device. A surface doped region is formed adjacent to the gate.

Fig. 1a